P-Channel 30-V (D-S) MOSFET

Key Features:

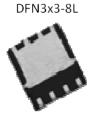
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

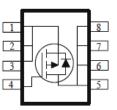
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY | | | | |
|---------------------|------------------------------|--------------------|--|--|
| V _{DS} (V) | $r_{DS(on)}(m\Omega)$ | I _D (A) | | |
| -30 | 20 @ V _{GS} = -10V | -10.9 | | |
| -30 | 36 @ V _{GS} = -4.5V | -8.1 | | |









| ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ | °C UNLESS OTH | ERWISE NO | TED) | | |
|--|----------------------|-----------------------------------|------------|-------|--|
| Parameter | | Symbol | Limit | Units | |
| Drain-Source Voltage | | | -30 | V | |
| Gate-Source Voltage | | V_{GS} | ±20 | V | |
| Continuous Dunis Commental | T _A =25°0 | ; | -10.9 | | |
| Continuous Drain Current a | T _A =70°0 | . I _D | -8.2 | Α | |
| Pulsed Drain Current ^b | | I _{DM} | -50 | | |
| Continuous Source Current (Diode Conduction) a | | I _S | -4.5 | Α | |
| Device Discipation 8 | T _A =25°0 | P _D | 3.5 | W | |
| Power Dissipation ^a | T _A =70°0 | | 2 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|--------------|-----------------|-------|------|--|--|--|
| Parameter | Symbol | Maximum | Units | | | | |
| Maximum Junction-to-Ambient ^a | t <= 10 sec | $R_{\theta JA}$ | 35 | °C/W | | | |
| Maximum Junction-to-Ambient | Steady State | VθJΑ | 81 | C/VV | | | |

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

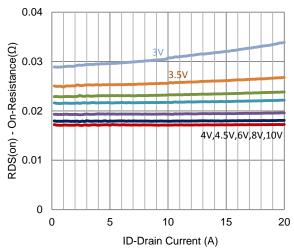
| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit | |
|---------------------------------|---------------------|---|-----|-------|------|-------|--|
| Static | | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$ | -1 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | |
| Zero Gate Voltage Drain Current | 1 | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$ | | | -1 | uA | |
| Zero Gate Voltage Brain Current | I _{DSS} | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | -25 | | |
| On-State Drain Current | I _{D(on)} | $V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$ | -15 | | | Α | |
| Drain-Source On-Resistance | r | $V_{GS} = -10 \text{ V}, I_{D} = -8.7 \text{ A}$ | | | 20 | mΩ | |
| Dialii-Source Ori-Nesistance | r _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$ | | | 36 | 11122 | |
| Forward Transconductance | g _{fs} | $V_{DS} = -15 \text{ V}, I_{D} = -8.7 \text{ A}$ | | 20 | | S | |
| Diode Forward Voltage | V_{SD} | $I_S = -2.3 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.76 | | V | |
| | | Dynamic | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$ | | 22 | | | |
| Gate-Source Charge | Q_{gs} | $I_{DS} = -13 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -8.7 \text{ A}$ | | 6.5 | | nC | |
| Gate-Drain Charge | Q_{gd} | 1B = 0.7 A | | 9.8 | | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DS} = -15 \text{ V}, R_{L} = 1.8 \Omega,$ | | 8 | | | |
| Rise Time | t _r | $V_{DS} = -13 \text{ V}, K_L - 1.8 \Omega,$ $I_D = -8.7 \text{ A},$ | | 35 | | no | |
| Turn-Off Delay Time | t _{d(off)} | $V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$ | | 85 | | ns | |
| Fall Time | t _f | V GEN = 10 V, 1 (GEN = 0.12 | | 51 | | | |
| Input Capacitance | C _{iss} | | | 1794 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 242 | | pF | |
| Reverse Transfer Capacitance | C_{rss} | | | 224 | | | |

Notes

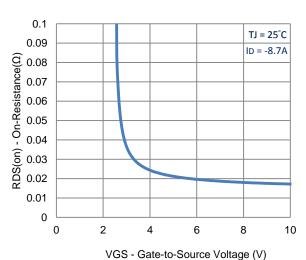
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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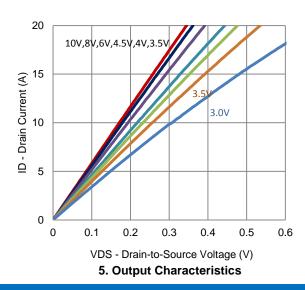
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage

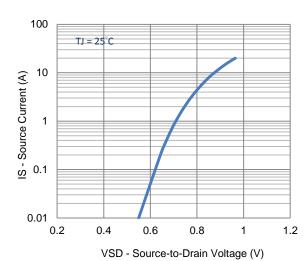


20
TJ = 25°C

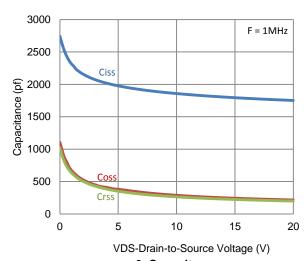
(Y) tueston 10
Uisurd 10
0 0 1 2 3 4

VGS - Gate-to-Source Voltage (V)

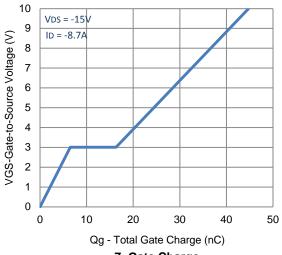
2. Transfer Characteristics

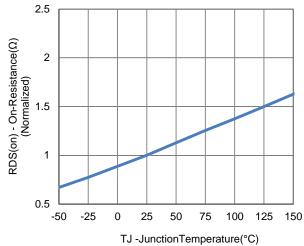


4. Drain-to-Source Forward Voltage



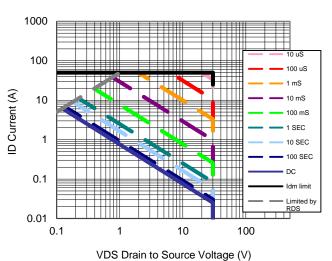
Typical Electrical Characteristics

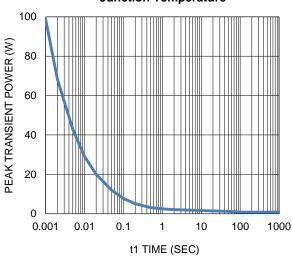




7. Gate Charge

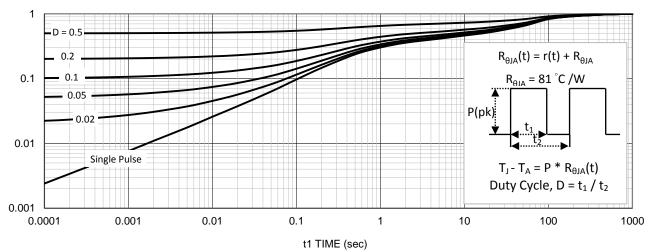






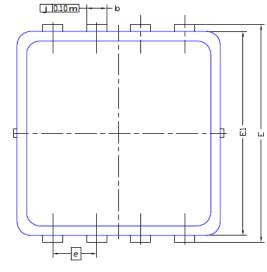
9. Safe Operating Area

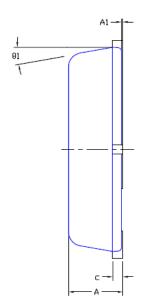
10. Single Pulse Maximum Power Dissipation

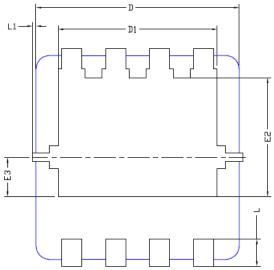


11. Normalized Thermal Transient Junction to Ambient

Package Information







| птм | MILLIMETERS | | | INCHES | | | |
|------|-------------|----------|-------|-----------|-----------|--------|--|
| DIM, | NIM | NDM | MAX | MIN | NDM | MAX | |
| Α | 0,700 | 0,80 | 0.900 | 0,0276 | 0,0315 | 0.0354 | |
| A1 | 0.00 | - | 0,05 | 0,000 | | 0'005 | |
| b | 0.24 | 0.30 | 0.35 | 0.009 | 0.012 | 0.014 | |
| С | 0.10 | 0.152 | 0.25 | 0.004 | 0.006 | 0.010 | |
| D | 3.00 BSC | | | 0.118 BSC | | | |
| D1 | 2,35 BSC | | | 0.093 BSC | | | |
| Ε | (3 | 3'50 B2C | | | 0.126 BSC | | |
| E1 | 3 | 3'00 B2C | | | 0.118 BSC | | |
| E2 | 1.75 BSC | | | 0.069 BSC | | | |
| E3 | 0,575 BSC | | | 0.023 BSC | | | |
| е | 0.65 BSC | | | 0.026 BSC | | | |
| L | 0,30 | 0,40 | 0,50 | 0,0118 | 0,0157 | 0.0197 | |
| L1 | 0 | | 0.100 | 0 | | 0.004 | |
| 91 | 0° | 10° | 12° | 0° | 10° | 12° | |